



睿晶科技股份有限公司
SILICON WORKS TECH CORPORATION

Cavity SOI SPEC

Growth method	Cz, MCz,
Diameter	200 mm, 150 mm
Crystal orientation	<100>, <111>
N type dopants	Antimony, Phosphorus, Arsenic
P type dopants	Boron
Resistivity	From 0.0008 to 100 Ohm-cm
Device layer thickness	From 5 μm to 100 μm
	Tolerance $\pm 0.5 \mu\text{m}$ (Cavity-SOI)
Buried oxide layer thickness	From 0.1 μm to 6 μm
Handle wafer thickness	200 mm: 400 μm to 1000 μm
	150 mm: 400 μm to 1000 μm
Back surface	Polished or etched
Terrace area	Standard or Terrace Free



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